

EUROPEAN PATENT OFFICE

Patent Abstracts of Japan

PUBLICATION NUMBER : 08264731
PUBLICATION DATE : 11-10-96

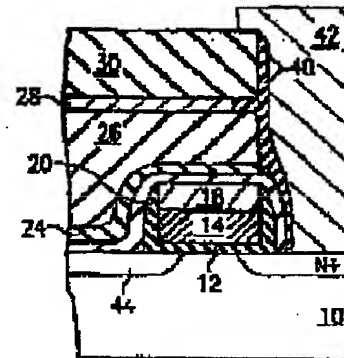
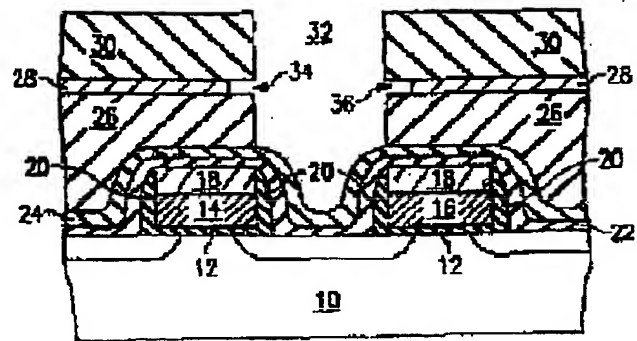
APPLICATION DATE : 04-01-96
APPLICATION NUMBER : 08000107

APPLICANT : TEXAS INSTR INC <TI>;

INVENTOR : LIU JIANN;

INT.CL. : H01L 27/108 H01L 21/8242 H01L 21/28
H01L 21/768

TITLE : SEMICONDUCTOR DEVICE AND ITS
MANUFACTURE



ABSTRACT : PROBLEM TO BE SOLVED: To provide a semiconductor device and its manufacturing method with which the generation of a defective device and the loss of production can be reduced or removed.

SOLUTION: A contact hole 32 is formed penetrating a conductive layer 28. Then, the conductive layer 28 is undercut (34 and 36). An insulating layer 40 is formed in the contact hole 32. Then, a contact point 42 is formed in the contact hole 32.

COPYRIGHT: (C)1996,JPO